



DS1249Y/AB

2048K Nonvolatile SRAM

FEATURES

- 10 years minimum data retention in the absence of external power
- Data is automatically protected during power loss
- Unlimited write cycles
- Low-power CMOS operation
- Read and write access times as fast as 70 ns
- Lithium energy source is electrically disconnected to retain freshness until power is applied for the first time
- Full $\pm 10\%$ V_{CC} operating range (DS1249Y)
- Optional $\pm 5\%$ V_{CC} operating range (DS1249AB)
- Optional industrial temperature range of -40°C to $+85^{\circ}\text{C}$, designated IND
- JEDEC standard 32-pin DIP package

PIN ASSIGNMENT

NC	1	32	V_{CC}
A16	2	31	A15
A14	3	30	A17
A12	4	29	\overline{WE}
A7	5	28	A13
A6	6	27	A8
A5	7	26	A9
A4	8	25	A11
A3	9	24	\overline{OE}
A2	10	23	A10
A1	11	22	\overline{CE}
A0	12	21	DQ7
DQ0	13	20	DQ6
DQ1	14	19	DQ5
DQ2	15	18	DQ4
GND	16	17	DQ3

32-PIN ENCAPSULATED PACKAGE
740 MIL EXTENDED

PIN DESCRIPTION

A0 – A17	– Address Inputs
DQ0 – DQ7	– Data In/Data Out
\overline{CE}	– Chip Enable
\overline{WE}	– Write Enable
\overline{OE}	– Output Enable
V_{CC}	– Power (+5V)
GND	– Ground
NC	– No Connect

DESCRIPTION

The DS1249 2048K Nonvolatile SRAMs are 2,097,152-bit, fully static, nonvolatile SRAMs organized as 262,144 words by 8 bits. Each NV SRAM has a self-contained lithium energy source and control circuitry which constantly monitors V_{CC} for an out-of-tolerance condition. When such a condition occurs, the

lithium energy source is automatically switched on and write protection is unconditionally enabled to prevent data corruption. There is no limit on the number of write cycles which can be executed and no additional support circuitry is required for microprocessor interfacing.

READ MODE

The DS1249 devices execute a read cycle whenever \overline{WE} (Write Enable) is inactive (high) and \overline{CE} (Chip Enable) and \overline{OE} (Output Enable) are active (low). The unique address specified by the 18 address inputs ($A_0 - A_{17}$) defines which of the 262,144 bytes of data is accessed. Valid data will be available to the eight data output drivers within t_{ACC} (Access Time) after the last address input signal is stable, providing that \overline{CE} and \overline{OE} access times are also satisfied. If \overline{OE} and \overline{CE} access times are not satisfied, then data access must be measured from the later occurring signal (\overline{CE} or \overline{OE}) and the limiting parameter is either t_{CO} for \overline{CE} or t_{OE} for \overline{OE} rather than t_{ACC} .

WRITE MODE

The DS1249 devices execute a write cycle whenever the \overline{WE} and \overline{CE} signals are active (low) after address inputs are stable. The later occurring falling edge of \overline{CE} or \overline{WE} will determine the start of the write cycle. The write cycle is terminated by the earlier rising edge of \overline{CE} or \overline{WE} . All address inputs must be kept valid throughout the write cycle. \overline{WE} must return to the high state for a minimum recovery time (t_{WR}) before another cycle can be initiated. The OE control signal should be kept inactive (high) during write cycles to avoid bus contention. However, if the output drivers are enabled (\overline{CE} and \overline{OE} active) then \overline{WE} will disable the outputs in t_{ODW} from its falling edge.

DATA RETENTION MODE

The DS1249AB provides full functional capability for V_{CC} greater than 4.75 volts and write protects by 4.5 volts. The DS1249Y provides full functional capability for V_{CC} greater than 4.5 volts and write protects by 4.25 volts. Data is maintained in the absence of V_{CC} without any additional support circuitry. The nonvolatile static RAMs constantly monitor V_{CC} . Should the supply voltage decay, the NV SRAMs automatically write protects themselves, all inputs become "don't care," and all outputs become high impedance. As V_{CC} falls below approximately 3.0 volts, a power switching circuit connects the lithium energy source to RAM to retain data. During power-up, when V_{CC} rises above approximately 3.0 volts, the power switching circuit connects external V_{CC} to the RAM and disconnects the lithium energy source. Normal RAM operation can resume after V_{CC} exceeds 4.75 volts for the DS1249AB and 4.5 volts for the DS1249Y.

FRESHNESS SEAL

Each DS1249 device is shipped from Dallas Semiconductor with its lithium energy source disconnected, guaranteeing full energy capacity. When V_{CC} is first applied at a level greater than V_{TP} , the lithium energy source is enabled for battery backup operation.

ABSOLUTE MAXIMUM RATINGS*

Voltage on Any Pin Relative to Ground	–0.3V to +7.0V
Operating Temperature	0°C to 70°C, –40°C to +85°C for Ind parts
Storage Temperature	–40°C to +70°C, –40°C to +85°C for Ind parts
Soldering Temperature	260°C for 10 seconds

* This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operation sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods of time may affect reliability.

RECOMMENDED DC OPERATING CONDITIONS(t_A: See Note 10)

PARAMETER	SYMBOL	MIN	TYP	MAX	UNITS	NOTES
DS1249AB Power Supply Voltage	V _{CC}	4.75	5.0	5.25	V	
DS1249Y Power Supply Voltage	V _{CC}	4.5	5.0	5.5	V	
Logic 1	V _{IH}	2.2		V _{CC}	V	
Logic 0	V _{IL}	0.0		+0.8	V	

DC ELECTRICAL CHARACTERISTICS(t_A: See Note 10) (V_{CC}=5V ± 10% for DS1249Y)

PARAMETER	SYMBOL	MIN	TYP	MAX	UNITS	NOTES
Input Leakage Current	I _{IL}	–2.0		+2.0	µA	
I/O Leakage Current CE ≥ V _{IH} ≤ V _{CC}	I _{IO}	–2.0		+2.0	µA	
Output Current @ 2.4V	I _{OH}	–1.0			mA	
Output Current @ 0.4V	I _{OL}	2.0			mA	
Standby Current CE=2.2V	I _{CCS1}		1.0	1.5	mA	
Standby Current CE=V _{CC} –0.5V	I _{CCS2}		100	150	µA	
Operating Current	I _{CC01}			85	mA	
Write Protection Voltage (DS1249AB)	V _{TP}	4.50	4.62	4.75	V	
Write Protection Voltage (DS1249Y)	V _{TP}	4.25	4.37	4.50	V	

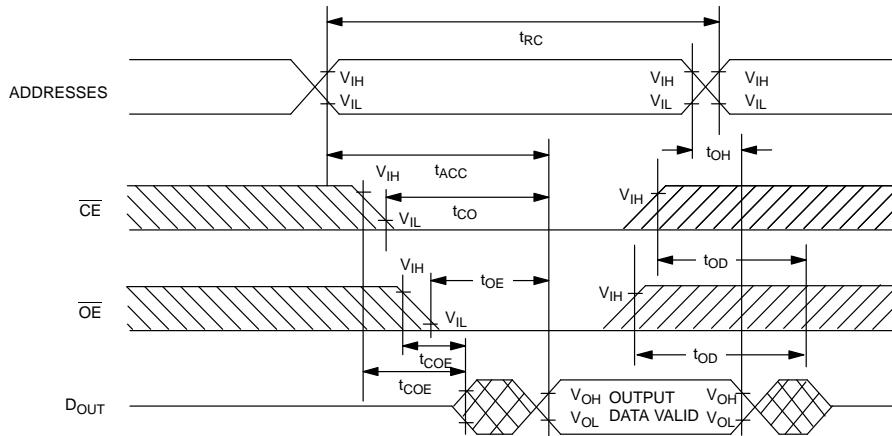
CAPACITANCE(t_A = 25°C)

PARAMETER	SYMBOL	MIN	TYP	MAX	UNITS	NOTES
Input Capacitance	C _{IN}		10	20	pF	
Input/Output Capacitance	C _{I/O}		10	20	pF	

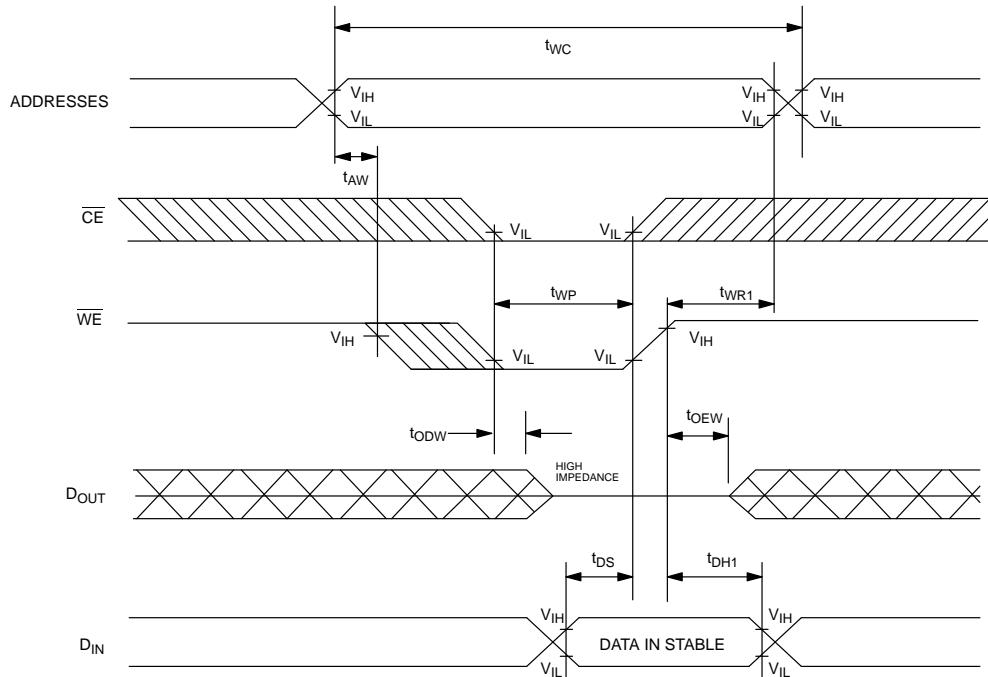
(V_{CC}=5V ± 5% for DS1249AB)
(t_A: See Note 10) (V_{CC}=5V ± 10% for DS1249Y)

AC ELECTRICAL CHARACTERISTICS

PARAMETER	SYMBOL	DS1249AB-70 DS1249Y-70		DS1249AB-100 DS1249Y-100		UNITS	NOTES
		MIN	MAX	MIN	MAX		
Read Cycle Time	t _{RC}	70		100		ns	
Access Time	t _{ACC}		70		100	ns	
OE to Output Valid	t _{OE}		35		50	ns	
CE to Output Valid	t _{CO}		70		100	ns	
OE or CE to Output Active	t _{COE}	5		5		ns	5
Output High-Z from Deselection	t _{OD}		25		35	ns	5
Output Hold from Address Change	t _{OH}	5		5		ns	
Write Cycle Time	t _{WC}	70		100		ns	
Write Pulse Width	t _{WP}	55		75		ns	3
Address Setup Time	t _{AW}	0		0		ns	
Write Recovery Time	t _{WR1} t _{WR2}	5 15		5 15		ns ns	12 13
Output High-Z from WE	t _{ODW}		25		35	ns	5
Output Active from WE	t _{OEW}	5		5		ns	5
Data Setup Time	t _{DS}	30		40		ns	4
Data Hold Time	t _{DH1} t _{DH2}	0 10		0 10		ns ns	12 13

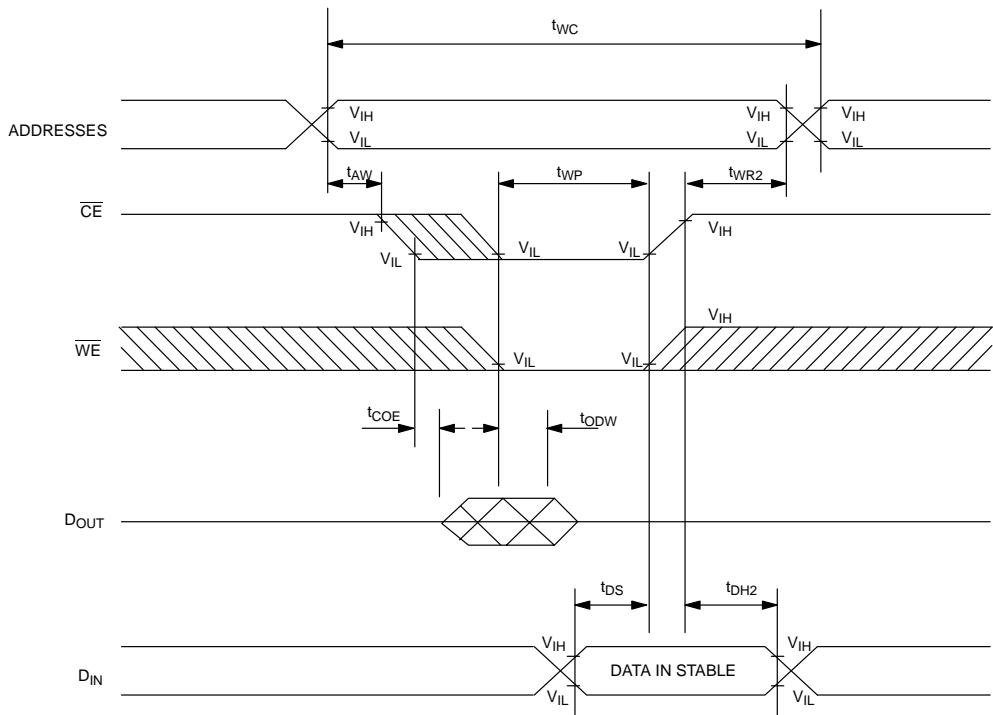
READ CYCLE

SEE NOTE 1

WRITE CYCLE 1

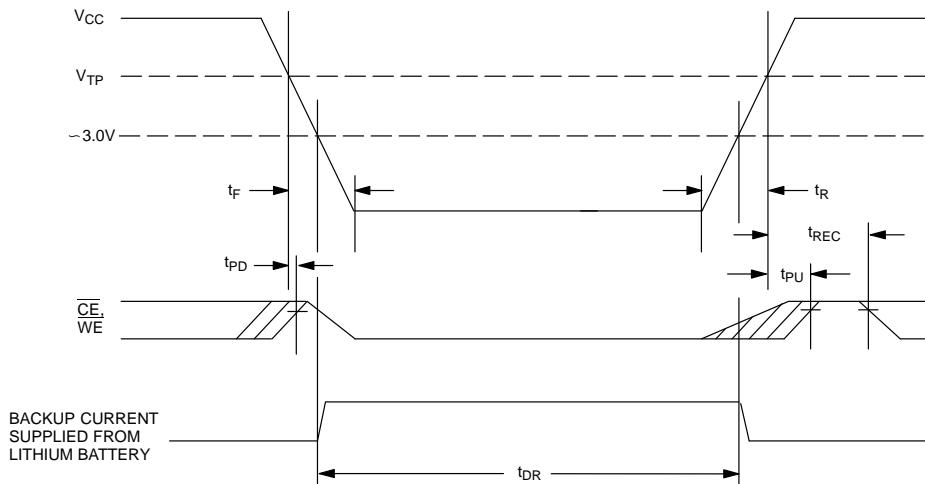
SEE NOTES 2, 3, 4, 6, 7, 8, and 12

WRITE CYCLE 2



SEE NOTES 2, 3, 4, 6, 7, 8 AND 13

POWER-DOWN/POWER-UP CONDITION



SEE NOTE 11

POWER-DOWN/POWER-UP TIMING(t_A: See Note 10)

PARAMETER	SYMBOL	MIN	TYP	MAX	UNITS	NOTES
V _{CC} Fail Detect to \overline{CE} and \overline{WE} Inactive	t _{PD}			1.5	μs	11
V _{CC} Slew from V _{TP} to 0V	t _F	150			μs	
V _{CC} Slew from 0V to V _{TP}	t _R	150			μs	
V _{CC} Valid to \overline{CE} and \overline{WE} Inactive	t _{PU}			2	ms	
V _{CC} Valid to End of Write Protection	t _{REC}			125	ms	

(t_A = 25°C)

PARAMETER	SYMBOL	MIN	TYP	MAX	UNITS	NOTES
Expected Data Retention Time	t _{DR}	10			years	9

WARNING:

Under no circumstance are negative undershoots, of any amplitude, allowed when device is in battery backup mode.

NOTES:

1. \overline{WE} is high throughout read cycle.
2. $\overline{OE} = V_{IH}$ or V_{IL} . If $\overline{OE} = V_{IH}$ during write cycle, the output buffers remain in a high impedance state.
3. t_{WP} is specified as the logical AND of \overline{CE} and \overline{WE} . t_{WP} is measured from the latter of \overline{CE} or \overline{WE} going low to the earlier of \overline{CE} or \overline{WE} going high.
4. t_{DS} is measured from the earlier of \overline{CE} or \overline{WE} going high.
5. These parameters are sampled with a 5 pF load and are not 100% tested.
6. If the \overline{CE} low transition occurs simultaneously with or later than the \overline{WE} low transition in Write Cycle 1, the output buffers remain in a high impedance state during this period.
7. If the \overline{CE} high transition occurs prior to or simultaneously with the \overline{WE} high transition, the output buffers remain in high impedance state during this period.
8. If \overline{WE} is low or the \overline{WE} low transition occurs prior to or simultaneously with the \overline{CE} low transition, the output buffers remain in a high impedance state during this period.
9. Each DS1249 has a built-in switch that disconnects the lithium source until V_{CC} is first applied by the user. The expected t_{DR} is defined as accumulative time in the absence of V_{CC} starting from the time power is first applied by the user.
10. All AC and DC electrical characteristics are valid over the full operating temperature range. For commercial products, this range is 0°C to 70°C for industrial products (IND), this range is -40°C to +85°C.
11. In a power down condition the voltage on any pin may not exceed the voltage on V_{CC}.
12. t_{WR1}, t_{DH1} are measured from \overline{WE} going high.
13. t_{WR2}, t_{DH2} are measured from \overline{CE} going high.

DC TEST CONDITIONS

Outputs Open

Cycle = 200 ns for operating current

All voltages are referenced to ground

AC TEST CONDITIONS

Output Load: 100 pF + 1 TTL Gate

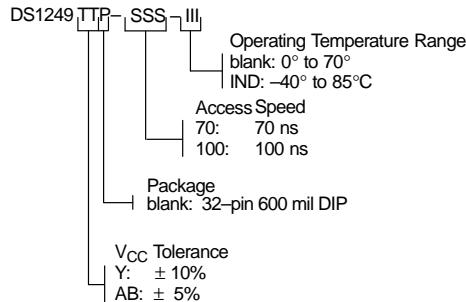
Input Pulse Levels: 0V to 3.0V

Timing Measurement Reference Levels

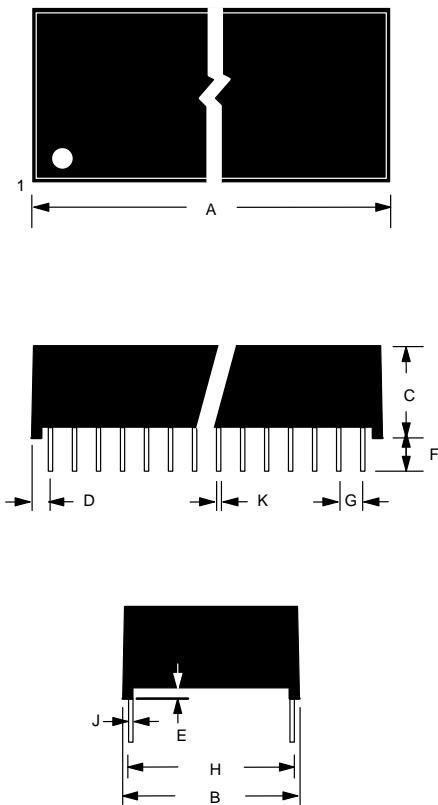
Input: 1.5V

Output: 1.5V

Input pulse Rise and Fall Times: 5 ns

ORDERING INFORMATION

DS1249Y/AB NONVOLATILE SRAM, 32-PIN 740 MIL EXTENDED MODULE



PKG	32-PIN	
DIM	MIN	MAX
A IN. MM	2.080 52.83	2.100 53.34
B IN. MM	0.715 18.16	0.740 18.80
C IN. MM	0.395 10.03	0.405 10.29
D IN. MM	0.280 7.11	0.310 7.49
E IN. MM	0.015 0.38	0.030 0.76
F IN. MM	0.120 3.05	0.160 4.06
G IN. MM	0.090 2.29	0.110 2.79
H IN MM	0.590 14.99	0.630 16.00
J IN MM	0.008 0.20	0.012 0.30
K IN. MM	0.015 0.43	0.025 0.58